What is claimed is:

1. A method for producing magneto resistive heads comprising the steps of:

positioning at least two magneto resistive elements in spaced relation to one another;

placing the at least two magneto resistive elements in an environment where material is removed nonselectively from items in the environment;

monitoring a property of at least two of the plurality of magneto resistive elements; and

dynamically covering one of the at least two magneto resistive elements to prevent additional removal of material from the covered magneto resistive element in response to the monitoring step.

2. The method of claim 1 wherein the monitoring step further comprises the steps of:

electrically connecting the at least two magneto resistive elements; and

measuring the electrical resistance of the at least two magneto resistive elements.

3. The method of claim 2 wherein the dynamically covering step takes place when the electrical resistance meets a selected level.

4. The method of claim 1 wherein the placing step includes placing the at least two magneto resistive elements in an ion milling environment.

5. The method of claim 4 wherein the step of dynamically covering one of the at least two of the magneto resistive elements further comprises actuating a shutter to substantially cover one of the at least two magneto resistive elements during ion milling.

6. The method of claim 1 wherein the step of dynamically covering one of the at least two of the magneto resistive elements further comprises actuating a shutter to substantially cover one of the at least two magneto resistive elements.

7. The method of claim 6 wherein the shutter has a width that is larger than the width of one magneto resistive element.

8. An apparatus for use in semiconductor fabrication comprising:

a carrier;

an elongated element held by the carrier; and

a dynamic mask that can be used to selectively cover a first portion of the elongated element as the semiconductor process continues to act on a second portion of the elongated element, the semiconductor process substantially halting with respect to the first portion of the elongated element.

9. The apparatus of claim 8 wherein the dynamic mask further comprises:

a first shutter;

a second shutter; and

an actuator for moving the first shutter and the second shutter.

10. The apparatus of claim 9 further comprising a controller for the actuator, the controller actuating each of the first shutter and the second shutter between an open position where the shutter is not covering a portion of the elongated element and a covering position where the shutter is covering a portion of the elongated element.

11. The apparatus of claim 9 further comprising:

a controller for the actuator, the controller actuating each of the first shutter and the second shutter between an open position where the shutter is not covering a

portion of the elongated element and a covering position where the shutter is covering a portion of the elongated element; and

a mechanism for measuring a property associated with a selected portion of the elongated element, wherein the controller actuates the first shutter and the second shutter in response to a selected value of a measured property.

12. The apparatus of claim 9 wherein the elongated element is a row of a plurality of magneto resistive elements sliced from a wafer.

13. The apparatus of claim 12 wherein at least two of the magneto resistive elements of the row of a plurality of magneto resistive elements are monitored for electrical resistance, the apparatus further comprising a controller for the actuator, the controller actuating each of the first shutter and the second shutter between an open position where the at least one of the first and second shutter is not covering a portion of the elongated element, and a covering position where the at least one of the first and second shutter is covering a portion of the elongated element, in response to the electrical resistance associated with that portion of the elongated element being at a predefined value.

14. The apparatus of claim 13 wherein the first shutter has a width larger than the width of at least one magneto resistive element.

15. The apparatus of claim 13 wherein the first shutter has a width larger than the width of one magneto resistive element and less than the width of two magneto resistive elements.

16. The apparatus of claim 13 wherein the first shutter has a width larger than the width of at least two magneto resistive elements.

17. The apparatus of claim 13 wherein the electrical resistance is measured during the semiconductive process of ion milling.

18. The apparatus of claim 17 wherein the electrical resistance is measured during the semiconductive process of ion milling and wherein the controller moves at least one of the first shutter and the second shutter over at least one of the magneto resistive elements during the process of ion milling, wherein the shutter has a width to substantially protect the magneto resistive element below the shutter from removal of material when the shutter is placed in a covering position over the magneto resistive element.

19. The apparatus of claim 12 wherein a magneto resistive element selected from the plurality of magincludes a stripe having a stripe height, the resistance measured across a magneto resistive element is related to the stripe height.

20. An apparatus for use during a semiconductor fabrication process comprising:

a target;

means for covering a portion of a target to prevent exposure of the portion of the target from the semiconductor fabrication process while an uncovered portion remains subjected to the semiconductor process.